

CLAIM AMENDMENTS

1. (Currently Amended) A method of manufacturing a semiconductor device ~~using~~ including a gallium nitride related semiconductor material, the method comprising:

~~a step of preparing a substrate whose having a surface that is formed by a gallium nitride related semiconductor material;~~

~~a nitriding step of contacting the surface with atom state nitrogen which is obtained by decomposing a nitrogen-containing gas by means of in a catalytic reaction, to thereby produce atomic nitrogen;~~

contacting the surface with the atomic nitrogen to nitride the surface; and

~~an electrode forming step of forming, on the surface, a gate electrode and source and drain electrodes opposing each other through~~ on opposite sides of the gate electrode.

2. (Currently Amended) ~~A~~ The method according to claim 1, wherein including:
in the nitriding step is a step at which, selectively nitriding the surface is selectively
nitrided, and

forming the electrode ~~forming step is a step at which the electrodes are formed on the surface thus selectively nitrided.~~

3. (Currently Amended) ~~A~~ The method according to claim 1, wherein including, in
the nitriding step is a step at which, forming an aluminum layer is formed on the surface and
nitriding a surface of the aluminum layer is nitrided.

4. (Currently Amended) A method of manufacturing a semiconductor device ~~using~~ including a gallium nitride related semiconductor material, the method comprising:

~~a step of preparing a substrate whose having a surface that is formed by a gallium nitride related semiconductor material;~~

~~a step of forming, on the surface, a gate electrode and source and drain electrodes opposing to each other through~~ on opposite sides of the gate electrode;

decomposing a nitrogen-containing gas in a catalytic reaction to produce atomic nitrogen; and

~~a nitriding step of contacting the surface, at an area between the source electrode and the gate electrode and at an area between the drain electrode and the gate electrode, with atom state the atomic nitrogen which is obtained by decomposing nitrogen-containing gas by means of a catalytic reaction, to thereby nitride the surface.~~

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5. (Currently Amended) ~~A~~ The method according to claim 4, wherein including, in the nitriding step is a step at which, forming an aluminum layer is formed on the surface and nitriding a surface of the aluminum layer is nitrided.

6. (Currently Amended) A method of manufacturing a semiconductor device ~~using~~ including a gallium nitride related semiconductor material, the method comprising:

~~a step of preparing a substrate whose having a surface that is formed by a gallium nitride related semiconductor material;~~

~~a step of forming, on the surface, a gate electrode and source and drain electrodes opposing each other through on opposite sides of the gate electrode;~~

~~a step of forming one of an insulation or insulating film and an aluminum film so as to cover covering all of the entire surface;~~

decomposing a nitrogen-containing gas in a catalytic reaction to produce atomic nitrogen; and

~~a nitriding step of contacting the surface, at an area between the source electrode and the gate electrode and at an area between the drain electrode and the gate electrode, with atom-state the atomic nitrogen which is obtained by decomposing nitrogen-containing gas by means of a catalytic reaction, to thereby nitride the surface.~~

7. (Currently Amended) ~~A~~ The method according to Claim 6, wherein, in the nitriding step is a step at which, the atom-state atomic nitrogen transmitted by the insulation or aluminum film is brought into contact with contacts the surface and so the surface is thereby nitrided.